

# N-channel TrenchMOS standard level FET Rev. 03 — 26 January 2011

Product data sheet

#### **Product profile** 1.

#### 1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

#### 1.2 Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance
- Suitable for standard level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

#### 1.3 Applications

- 12 V and 24 V loads
- Automotive systems

- General purpose power switching
- Motors, lamps and solenoids

#### 1.4 Quick reference data

Table 1.         Quick reference data						
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	-	55	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; see <u>Figure 3</u> ; see <u>Figure 1</u>	-	-	11	А
P <sub>tot</sub>	total power dissipation	$T_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 2}}{\text{Figure 2}}$	-	-	36	W
Static cha	aracteristics					
$R_{DSon}$	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 5 A; T <sub>j</sub> = 25 °C; see <u>Figure 10</u> ; see <u>Figure 11</u>	-	127	150	mΩ



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Table 1.	Quick reference da	tacontinued					
Symbol	Parameter	Conditions	N	/lin	Тур	Max	Unit
Avalanch	e ruggedness						
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$ \begin{split} I_D &= 11 \text{ A};  \text{V}_{\text{sup}} \leq 55 \text{ V}; \\ R_{\text{GS}} &= 50  \Omega;  \text{V}_{\text{GS}} = 10 \text{ V}; \\ T_{j(\text{init})} &= 25 ^{\circ}\text{C}; \text{ unclamped} \end{split} $	-		-	16	mJ
Dynamic	characteristics						
$Q_{GD}$	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 3 \text{ A};$ $V_{DS} = 44 \text{ V}; T_j = 25 \text{ °C};$ see <u>Figure 12</u>	-		2.7	-	nC

### 2. Pinning information

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain <sup>[1]</sup>	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT428 (DPAK)	

[1] It is not possible to make a connection to pin 2.

### 3. Ordering information

#### Table 3.Ordering information

Type number	Package		
	Name	Description	Version
BUK72150-55A	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428

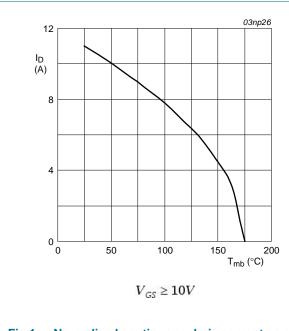
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### 4. Limiting values

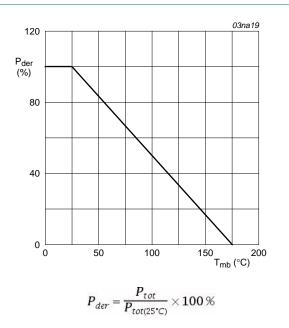
#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	55	V
V <sub>DGR</sub>	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$	-	55	V
V <sub>GS</sub>	gate-source voltage		-20	20	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 10 V; see <u>Figure 3</u> ; see <u>Figure 1</u>	-	11	А
		$T_{mb}$ = 100 °C; $V_{GS}$ = 10 V; see <u>Figure 1</u>	-	7	А
I <sub>DM</sub>	peak drain current	T <sub>mb</sub> = 25 °C; pulsed; t <sub>p</sub> ≤ 10 μs; see <u>Figure 3</u>	-	44	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	36	W
T <sub>stg</sub>	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-drain	diode				
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	-	11	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu$ s; $T_{mb} = 25 \ ^{\circ}C$	-	44	А
Avalanche ru	ggedness				
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D$ = 11 A; $V_{sup} \le 55$ V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; unclamped	-	16	mJ



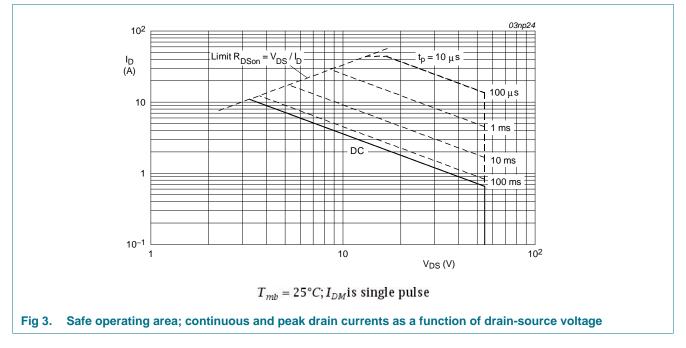






## **BUK72150-55A**

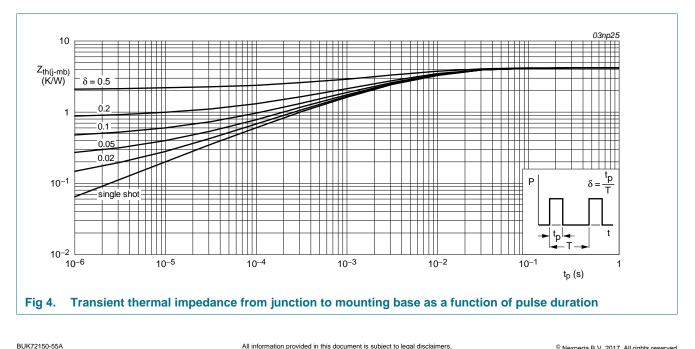
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#### **Thermal characteristics** 5.

#### Table 5. **Thermal characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	see <u>Figure 4</u>	-	-	4.1	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient		-	71	-	K/W



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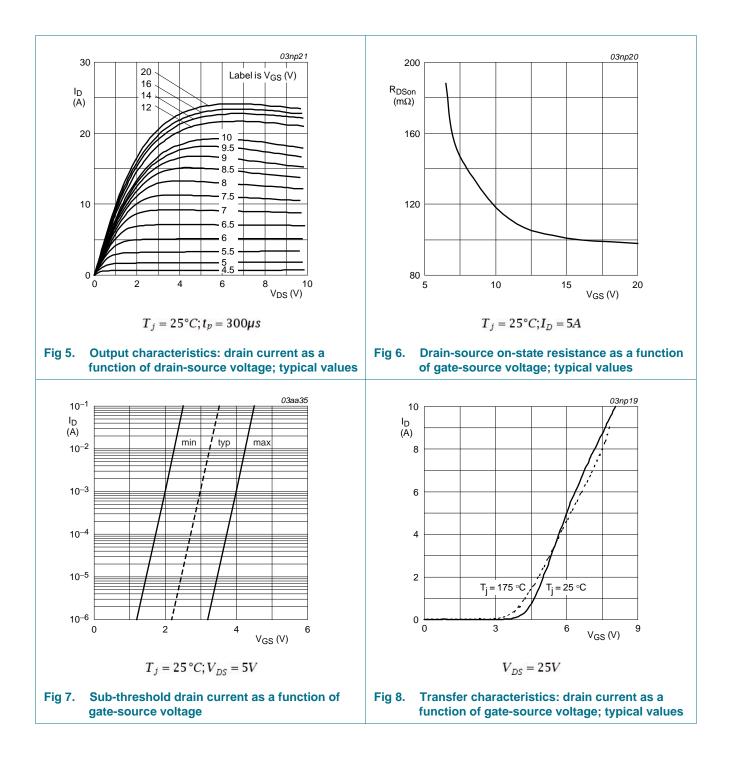
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### 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static cha	aracteristics					
V <sub>(BR)DSS</sub>	drain-source	$I_D = 0.25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	50	-	-	V
	breakdown voltage	$I_D = 0.25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	55	-	-	V
V <sub>GS(th)</sub> gate-source thresho voltage	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 9</u>	2	3	4	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 175 °C; see <u>Figure 9</u>	1	-	-	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = -55 °C; see <u>Figure 9</u>	-	-	4.4	V
DSS	drain leakage current	V <sub>DS</sub> = 55 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	-	-	500	μA
		V <sub>DS</sub> = 55 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.05	10	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; \text{ T}_{j} = 25 \text{ °C}$	-	2	100	nA
$R_{DSon}$	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 175 °C; see <u>Figure 10</u> ; see <u>Figure 11</u>	-	-	300	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 25 °C; see <u>Figure 10</u> ; see <u>Figure 11</u>	-	127	150	mΩ
Dynamic	characteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 3 \text{ A}; V_{DS} = 44 \text{ V}; V_{GS} = 10 \text{ V};$	-	5.5	-	nC
Q <sub>GS</sub>	gate-source charge	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 12}{\text{Figure } 12}$	-	1	-	nC
Q <sub>GD</sub>	gate-drain charge		-	2.7	-	nC
C <sub>iss</sub>	input capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 25 V; f = 1 MHz;	-	242	322	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; see <u>Figure 13</u>	-	40	48	pF
C <sub>rss</sub>	reverse transfer capacitance		-	25	35	pF
d(on)	turn-on delay time	$V_{DS} = 25 \text{ V}; \text{ R}_{L} = 2.7 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	3	-	ns
tr	rise time	$R_{G(ext)} = 5.6 \ \Omega; \ T_{j} = 25 \ ^{\circ}C$	-	26	-	ns
d(off)	turn-off delay time		-	8	-	ns
t <sub>f</sub>	fall time	$V_{DS}$ 25 V; $R_L = 2.7 \Omega$ ; $V_{GS} = 10$ V; $R_{G(ext)} = 5.6 \Omega$ ; $T_j = 25 \text{ °C}$	-	10	-	ns
L <sub>D</sub>	internal drain inductance	measured from drain to center of die ; $T_j = 25 ^{\circ}\text{C}$	-	2.5	-	nH
-s	internal source inductance	measured from source lead to source bond pad ; $T_j = 25 \text{ °C}$	-	7.5	-	nH
Source-d	rain diode					
V <sub>SD</sub>	source-drain voltage	$I_S = 10 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C};$ see Figure 14	-	1.25	1.5	V
·rr	reverse recovery time	$I_{\rm S} = 10 \text{ A}; \text{ dI}_{\rm S}/\text{dt} = -100 \text{ A}/\mu\text{s};$	-	32	-	ns
Q <sub>r</sub>	recovered charge	$V_{GS}$ = -10 V; $V_{DS}$ = 30 V; $T_j$ = 25 °C	-	50	-	nC

## BUK72150-55A

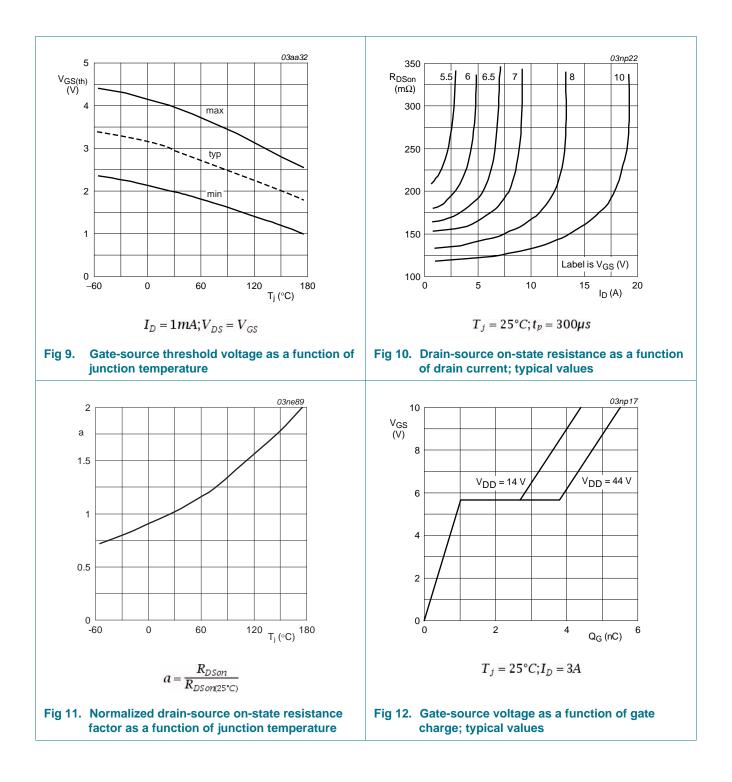
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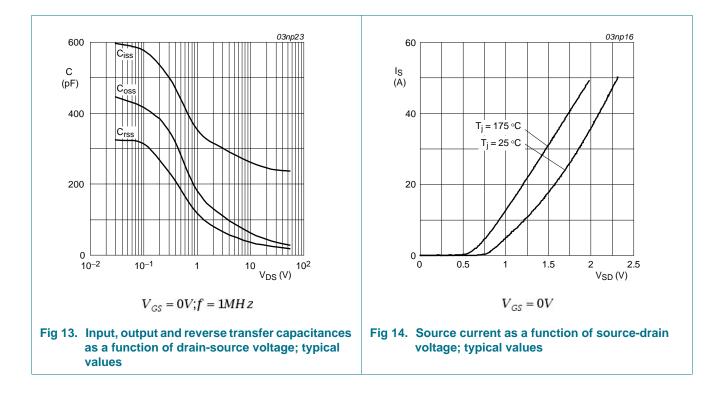
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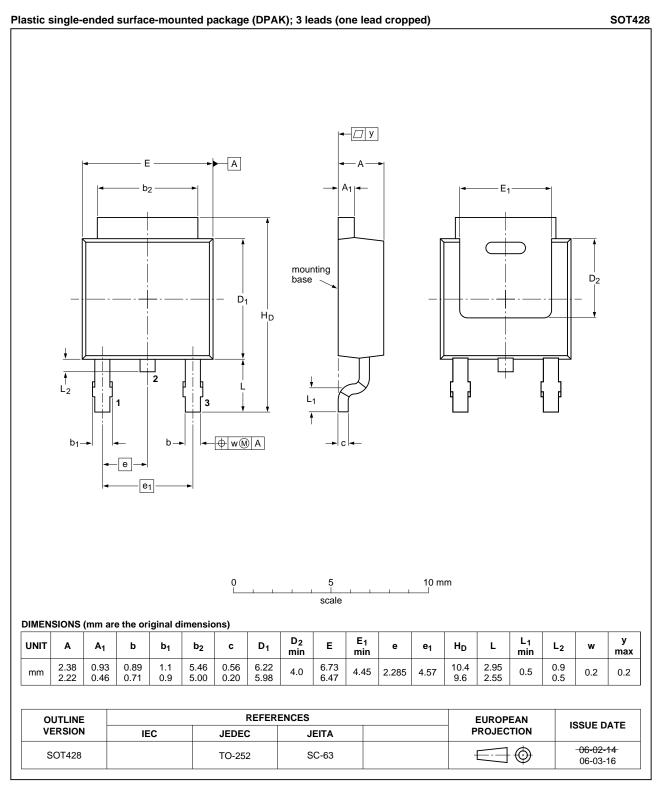
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#### 7. Package outline



#### Fig 15. Package outline SOT428 (DPAK)

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### 8. Revision history

Table 7. Revision l	history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK72150-55A v.3	20110126	Product data sheet	-	BUK72150-55A v.2
Modifications:	<ul> <li>The format of t of NXP Semice</li> </ul>	this data sheet has been rec onductors.	lesigned to comply with	the new identity guidelines
	<ul> <li>Legal texts have</li> </ul>	ve been adapted to the new	company name where	appropriate.
	<ul> <li>Various change</li> </ul>	es to content.		
BUK72150-55A v.2 (9397 750 12335)	20031120	Product data sheet	-	-

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#### 9. Legal information

#### 9.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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